



HIGH ELECTRON CONCENTRATION WAFERS

n-type

TECHNICAL SPECIFICATION		
Features	Units	Available planes
		C-plane (0001)
Carrier concentraton	cm ⁻³	~10 ¹⁹
Dopant		Oxygen
Resistvity	Ωcm	~10 ⁻³
Mobility	cm ² / Vs	~150
Thickness	μm	350 ±50
TTV	μm	≤40
Bow	μm	≤10
FWHM (0002) of XRC, (epi-ready; 0.1x0.1 mm slit)	arcsec	~20
Etch Pits Density (EPD)	cm ⁻²	~5x10 ⁴
Off-cut	deg	0.3±0.1 to the m-direction
Surface fnishing	Front side	epi-ready (RMS < 0.5 nm)
	Back side	rough
Available sizes		1-inch
		2-inch
Packaging		separate single wafer container
Special request		for pricing or technical enquiries please contact our sales team

